

# DIGITRON SEMICONDUCTORS

## S2800 SERIES

## SILICON CONTROLLED RECTIFIER

Available Non-RoHS (standard) or RoHS compliant (add PBF suffix).

Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.

### MAXIMUM RATINGS

| Rating                                                                                                                                     | Symbol                              | Value       | Unit             |
|--------------------------------------------------------------------------------------------------------------------------------------------|-------------------------------------|-------------|------------------|
| <b>Peak repetitive forward and reverse blocking voltage<sup>(1)</sup></b><br>(T <sub>J</sub> = 25 to 100°C, gate open)                     | V <sub>RRM</sub> , V <sub>DRM</sub> |             |                  |
| S2800F                                                                                                                                     |                                     | 50          | Volts            |
| S2800A                                                                                                                                     |                                     | 100         |                  |
| S2800B                                                                                                                                     |                                     | 200         |                  |
| S2800D                                                                                                                                     |                                     | 400         |                  |
| S2800M                                                                                                                                     |                                     | 600         |                  |
| S2800N                                                                                                                                     |                                     | 800         |                  |
| <b>Peak non-repetitive reverse voltage and non-repetitive off-state voltage<sup>(1)</sup></b><br>(T <sub>J</sub> = 25 to 100°C, gate open) | V <sub>RSM</sub> , V <sub>DSM</sub> |             |                  |
| S2800F                                                                                                                                     |                                     | 75          | Volts            |
| S2800A                                                                                                                                     |                                     | 125         |                  |
| S2800B                                                                                                                                     |                                     | 250         |                  |
| S2800D                                                                                                                                     |                                     | 500         |                  |
| S2800M                                                                                                                                     |                                     | 700         |                  |
| S2800N                                                                                                                                     |                                     | 900         |                  |
| <b>Forward on-state current RMS</b> (all conduction angles), T <sub>C</sub> = 75°C                                                         | I <sub>T(RMS)</sub>                 | 10          | Amps             |
| <b>Peak forward surge current</b><br>(one cycle, sine wave, 60Hz, T <sub>C</sub> = 80°C)                                                   | I <sub>TSM</sub>                    | 100         | Amps             |
| <b>Circuit fusing considerations</b><br>(t = 8.3ms)                                                                                        | I <sup>2</sup> t                    | 40          | A <sup>2</sup> s |
| <b>Forward peak gate power</b> (t ≤ 10μs)                                                                                                  | P <sub>GM</sub>                     | 16          | Watts            |
| <b>Forward average gate power</b>                                                                                                          | P <sub>G(AV)</sub>                  | 0.5         | Watts            |
| <b>Operating junction temperature range</b>                                                                                                | T <sub>J</sub>                      | -40 to +100 | °C               |
| <b>Storage temperature range</b>                                                                                                           | T <sub>stg</sub>                    | -40 to +150 | °C               |

Note 1: V<sub>DRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

### THERMAL CHARACTERISTICS

| Characteristic                              | Symbol           | Maximum | Unit |
|---------------------------------------------|------------------|---------|------|
| <b>Thermal resistance, junction to case</b> | R <sub>θJC</sub> | 2       | °C/W |

### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

| Characteristic                                                                                                                                                             | Symbol           | Min. | Typ. | Max. | Unit  |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------|------|------|------|-------|
| <b>Peak forward or reverse blocking current</b><br>(V <sub>AK</sub> = V <sub>DRM</sub> or V <sub>RRM</sub> , gate open)<br>T <sub>C</sub> = 25°C<br>T <sub>C</sub> = 100°C | I <sub>DRM</sub> | -    | -    | 10   | μA    |
|                                                                                                                                                                            |                  | -    | -    | 2    | mA    |
| <b>Instantaneous on-state voltage</b><br>(I <sub>TM</sub> = 30A peak, pulse width ≤ 1ms, duty cycle ≤ 2%)                                                                  | V <sub>T</sub>   | -    | 1.7  | 2    | Volts |
| <b>Gate trigger current (continuous dc)</b><br>(V <sub>D</sub> = 12V, R <sub>L</sub> = 30Ω)                                                                                | I <sub>GT</sub>  | -    | 8    | 15   | mA    |
| <b>Gate trigger voltage (continuous dc)</b><br>(V <sub>D</sub> = 12V, R <sub>L</sub> = 30Ω)                                                                                | V <sub>GT</sub>  | -    | 0.9  | 1.5  | Volts |
| <b>Holding current</b><br>(V <sub>D</sub> = 12V, gate open, I <sub>T</sub> = 150mA)                                                                                        | I <sub>H</sub>   | -    | 10   | 20   | mA    |
| <b>Gate controlled turn-on time</b><br>(V <sub>D</sub> = rated V <sub>DRM</sub> , I <sub>TM</sub> = 2A, I <sub>GR</sub> = 80mA)                                            | t <sub>gt</sub>  | -    | 1.6  | -    | μs    |

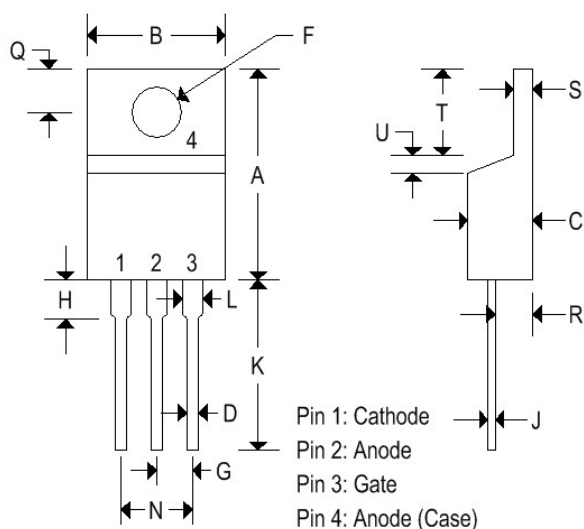
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| Characteristic                                                                                                                                                        | Symbol  | Min. | Typ. | Max. | Unit      |
|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------|------|------|------|-----------|
| <b>Circuit commutated turn-off time</b><br>$(V_D = V_{DRM}, I_{TM} = 2A, \text{ pulse width } \leq 50\mu s, dv/dt = 200V/\mu s, di/dt = 10A/\mu s, T_C = 75^\circ C)$ | $t_q$   | -    | 25   | -    | $\mu s$   |
| <b>Critical rate of rise of off-state voltage</b><br>$(V_D = \text{Rated } V_{DRM}, \text{ exponential rise, } T_C = 100^\circ C)$                                    | $dv/dt$ | -    | 100  | -    | $V/\mu s$ |

### MECHANICAL CHARACTERISTICS

|                |                             |
|----------------|-----------------------------|
| <b>Case</b>    | TO-220AB                    |
| <b>Marking</b> | Body painted, alpha-numeric |
| <b>Pin out</b> | See below                   |

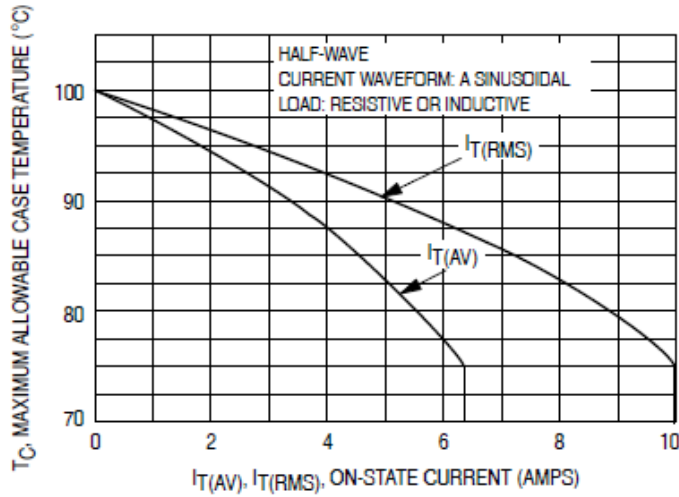


|   | TO-220AB |       |             |        |
|---|----------|-------|-------------|--------|
|   | Inches   |       | Millimeters |        |
|   | Min      | Max   | Min         | Max    |
| A | 0.575    | 0.620 | 14.600      | 15.750 |
| B | 0.380    | 0.405 | 9.650       | 10.290 |
| C | 0.160    | 0.190 | 4.060       | 4.820  |
| D | 0.025    | 0.035 | 0.640       | 0.890  |
| F | 0.142    | 0.147 | 3.610       | 3.730  |
| G | 0.095    | 0.105 | 2.410       | 2.670  |
| H | 0.110    | 0.155 | 2.790       | 3.930  |
| J | 0.014    | 0.022 | 0.360       | 0.560  |
| K | 0.500    | 0.562 | 12.700      | 14.270 |
| L | 0.045    | 0.055 | 1.140       | 1.390  |
| N | 0.190    | 0.210 | 4.830       | 5.330  |
| Q | 0.100    | 0.120 | 2.540       | 3.040  |
| R | 0.080    | 0.110 | 2.040       | 2.790  |
| S | 0.045    | 0.055 | 1.140       | 1.390  |
| T | 0.235    | 0.255 | 5.970       | 6.480  |
| U | -        | 0.050 | -           | 1.270  |
| V | 0.045    | -     | 1.140       | -      |
| Z | -        | 0.080 | -           | 2.030  |

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**FIGURE 1 – CURRENT DERATING**



**FIGURE 2 – POWER DISSIPATION**

